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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/770,699	01/26/2001	F. Daniel Gealy	98093DIV	7854
26285	7590	03/23/2005	EXAMINER	
KIRKPATRICK & LOCKHART NICHOLSON GRAHAM LLP 535 SMITHFIELD STREET PITTSBURGH, PA 15222				TRINH, MICHAEL MANH
ART UNIT		PAPER NUMBER		
		2822		

DATE MAILED: 03/23/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	09/770,699	GEALY ET AL. <i>(initials)</i>	
	Examiner	Art Unit	
	Michael Trinh	2822	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) Responsive to communication(s) filed on 02 February 2005.
- 2a) This action is FINAL. 2b) This action is non-final.
- 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) Claim(s) 38-43, 45-49 and 52-60 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) Claim(s) _____ is/are allowed.
- 6) Claim(s) 38-43, 45-49 and 52-60 is/are rejected.
- 7) Claim(s) _____ is/are objected to.
- 8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) The specification is objected to by the Examiner.
- 10) The drawing(s) filed on _____ is/are: a) accepted or b) objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) All b) Some * c) None of:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. _____.
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)	4) <input type="checkbox"/> Interview Summary (PTO-413)
2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Date. _____.
3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date _____.	5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152)
	6) <input type="checkbox"/> Other: _____.

DETAILED ACTION

*** This office action is in response to Applicant's RCE and amendment filed on February 02, 2005. Claims 38-43,45-49,52-60 are currently pending.

*** The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.

Claim rejections - 35 USC § 103

1. Claims 38-43,45-49,52-60 are rejected under 35 U.S.C. 103(a) as being unpatentable over Fukuzumi et al (6,222,722) taken with Chen et al (6,077,742) and New (5,824,590).

Fukuzumi et al teach a method for forming a capacitor comprising at least the steps of: forming on a substrate assembly; forming a layer of hemispherical grain polysilicon (re claims 52,58; 12 in Fig 11; col 9, line 45 through col 10; 51 in Figs 30-34; col 14, line 45 through col 15) in a recess of a substrate assembly including the layer (10 in Fig 11; 21/20 in Figs 22,27-29) and the layer (2 in Figs 11,22; 20/38 in Figs 27-29), wherein a portion of the substrate assembly is removed; forming a first electrode 13,24,52 on the hemispherical grain polysilicon recessed in the substrate assembly, wherein the first electrode 13,24,52 is selected from the group consisting of transition metal or a conductive metal oxide (13 in Fig 12; col 7, lines 40-60; 24 in Figs 27-29; or 52 in Figs 30-34); removing the hemispherical grain polysilicon 23,4 (Figs 22-23,4-5); forming a dielectric 14,26,53 on the first electrode, wherein the first electrode extends above an uppermost surface of a substrate assembly including the insulating interlayer (20 in Figs 27-29; or 66/10 in Fig 38), the insulating layer 2 and an interconnect 3 recessed in the assembly (Figs 6,24,26,27-29,38); and forming a second electrode (15 in Fig 13; 27 in Fig 29, 54 in Fig 33) having strap on the dielectric, wherein the dielectric is formed between the first and second electrodes, and wherein the first and second electrodes each include a non-smooth surface (Figs 13,29,33,34,38). Re claims 41-43,45, wherein the first electrode 13,24,52 of metal includes ruthenium, platinum, Ir, Rh and its metal oxide including RuO₂, wherein x = 2 (col 14, line 66 through col 15, line 10; col 9, lines 49-67; col 16, line 62 through col 7; col 20, lines 10-25), and wherein the second electrode 15,27,54 includes ruthenium, platinum, wherein material for forming the electrode including ruthenium, platinum, oxide thereof, or W, WN, Al, Ti, TaN (col 17, lines 12-18). Re claims 39-40,53-55, wherein forming the first electrode includes chemical vapor deposition (CVD) and planarization thereafter by CMP (13 in Fig 12; col 7, lines 40-60;

24 in Figs 22-23, col 11, line 65 through col 12; or 52 in Figs 30-34) on the hemispherical grain polysilicon. Re claims 46, wherein the second electrode 9,13,27,54 is formed by chemical vapor deposition (CVD) (col 8, lines 15-18). Re claims 47-48, wherein the dielectric 14,53 of an insulating metal oxide includes barium strontium titanate (BSTO), Ta_2O_5 , $SrTiO_3$, $BaSrTiO_3$ (col 17, lines 3-10). Re claim 56, wherein removing the hemispherical grain polysilicon 23,4 is shown in Figs 22-23,4-5. Re claims 49,57, wherein the substrate assembly is formed before forming the first electrode 13,24,52 (Figs 9-13,21-24,30-33). Re claim 59, the method includes forming an interconnect 3 recessed in the substrate assembly, wherein the first electrode 13,24,52 is formed in the interconnection recessed in the substrate assembly (Figs 1-5,21-24,33,38). Re claim 60, the method includes forming a contact 3 in the substrate assembly (Figs 21-24,33,38), and wherein the first electrode 13,24,52 is formed in the contact in the substrate assembly.

Fukuzumi already teaches forming the dielectric (8,14,26,53) on the first electrode (7,13,24,52) and on the uppermost surface of the substrate assembly 2, but lacks forming the second electrode (9,15,27,54) on the uppermost surface of the substrate assembly, and heating the dielectric in oxygen-containing ambient.

However, Chen teaches (at Figs 5-8; col 8, line 35 through col 9) forming a first electrode 36' in a recess of a substrate assembly and extending above the uppermost surface of the substrate assembly including an insulating layer 32/28 (Fig 5); forming a capacitor dielectric 40 on the first electrode 36' and the uppermost surface of the substrate assembly including the insulating layer 32/28; and forming the second electrode 42 on the dielectric 40 and the uppermost surface of the substrate assembly including the insulating layer 32/28, wherein as shown in Figure 8 of Chen (6,077,742), the second electrode 42 is having a non-smooth surface adjacent to the capacitor dielectric layer 40, and wherein the first electrode 36', the second electrode 42, and the capacitor dielectric layer 40 are all having at least one non-smooth surface. New teaches forming a capacitor dielectric on the first electrode, and heating the dielectric in the presence of an oxygen-containing ambient (at col 3, line 33-67; col 2, line 62 through col 3, line 19; col 1, lines 18-52).

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to form the capacitor of Fukuzumi by forming the capacitor dielectric layer on the first electrode, and forming the second electrode (9,15,27,54) entirely on the capacitor

dielectric layer and on the uppermost surface of the substrate assembly, as disclosed by Chen. This is because of the desirability to complete and facilitate the next level of electrical interconnections in forming an electrical contact to the second electrode 42 that is laterally extended from the first electrode, and formed on the uppermost surface of the substrate assembly including the insulating layer 32/28 (Chen, Fig 8; col 9, lines 55 through col 10, line 4). Forming the first electrode in a recess of the substrate assembly and extending above the uppermost surface of the substrate assembly, and forming the second electrode on the dielectric and on the uppermost surface of the substrate assembly are taught by the references and would have been obvious to one of ordinary skill in the art so that the first electrode is formed in a recess opening of a substrate assembly contacting the underlying conductive layer for electrically connection. Also, it would have been obvious to one of ordinary skill in the art at the time the invention was made to form the capacitor dielectric layer on the first electrode Fukuzumi, and at least heating the dielectric layer in the presence of oxygen-containing ambient, as taught by New. This is because of the desirability to oxidize and crystallize the dielectric layer in order to improve and achieve ferroelectric properties of the dielectric layer having high dielectric constant.

Re further claims 41-43,45,58, Fukuzumi already teaches several alternative materials for the electrodes or the dielectric, but does not list all materials as claimed. As to claims 38-43,45-49,52-57, Fukuzumi already teaches a method for forming a capacitor, wherein the first electrode 13,52 of metal includes ruthenium, platinum, Ir, Rh, and its metal oxide including RuO₂, wherein x = 2 (col 14, line 66 through col 15, line 10; col 9, lines 49-67; col 16, line 62 through col 7; col 20, lines 10-25), wherein the second electrode 15,54 includes ruthenium, platinum, wherein materials for forming the electrode include ruthenium, platinum, oxide thereof, or W, WN, Al, Ti, TaN (col 17, lines 12-18), wherein the dielectric 14,53 includes barium strontium titanate (BST), Ta₂O₅, SrTiO₃ , BaSrTiO₃ (col; 17, lines 3-10). New teaches forming the dielectric between the first and second electrodes, wherein the electrode includes a metal oxide of rubidium oxide, ruthenium dioxide (RuO₂, wherein x = 2), or IrO₂ (col 2, lines 55-61; col 4, lines 11-24), wherein the electrode includes platinum, Ru, TaN, WN, ,TiN, Ir, polysilicon, and wherein the dielectric includes barium strontium titanate, Sr(1-x)BixTiO₃, SrTiO₃, BaSrTiO₃ (col 3, lines 1-19). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to form the electrodes or the dielectric of Fukuzumi by using other alternative materials as well known in the semiconductor art and as taught by Fukuzumi and New. This is because the substitution of art recognized equivalent materials would have been obvious and within the level of ordinary skill in the semiconductor art, wherein these dielectric materials are having high dielectric constant, and wherein these

conductive materials are oxidation barrier and having high electrical conductivity. Re further claim 40, planarization after CVD forming the first electrode is taught by Fukuzumi (at Fig 4; col 7, lines 40-59), because of the desirability to isolate a plurality of lower electrodes one from each other, and to form stacked container capacitor having high capacitance.

Double Patenting

2. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

3. Claims 38-43,45-49,52-60 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over either Claims 81-113 of Application Serial No. 10/299,145; Claims 81-109 of U.S. Application Serial No. 10/299,752; or Claims 81-108 of U.S. Application Serial No. 10/299,728; and 81-87,89-103,106-112 of U.S. Application Serial No. 10/172,253.

Although the conflicting claims are not identical, they are not patentably distinct from each other. Claim 38 of this present application differs from, for example, claim 81 of applications 10/299,145; 10/299742; and 10299728 at least in that forming the first electrode in a recess of a substrate assembly. As similarly recited in claim 81 of applications 10/299,145; 10/299742; and 10299728, claim 38 of this application also recites forming the first electrode having at least one non-smooth surface, and claims 52,57 of this application also recite the first and second electrodes each include a non-smooth surface. However, forming the first electrode in a recess of a substrate assembly, forming the first electrode on a substrate assembly, forming the first electrode having at least one non-smooth surface, forming the second electrode having at

least one non-smooth surface, and/or forming a second substrate layer on the second electrode would have been obvious to one of ordinary skill in the art as taught by Prall (5,866,453) and/or Fukuzumi. This is because of the desirability to expose more surface of the capacitor first and second electrodes so as to increase capacitance of the capacitor, and because of the desirability to form different capacitor structures including in a recess of a substrate, on a planar surface of the substrate, partially recessed in the substrate assembly, as shown by Prall (5,866,453) or Fukuzumi. Additionally, claims 38,52,58 of this present application are also anticipated and broad enough to encompass the scope of claims 81-87,89-103,106-112 of the 10/172,253 application, in which first and second electrode each includes a non-smooth surface, and in which a layer of hemispherical grain polysilicon is formed in a recess opening of the substrate assembly and is used as a non-smooth molding. Furthermore, Kim (6,090,704; see Figure 3F) teaches forming an additional substrate oxide layer 118 having an opening, and forming in the opening an interconnect 124 for electrically connecting to the second electrode 112. Thus, it would have been obvious to one of ordinary skill in the art to complete fabrication of a capacitor of Fukuzumi (6,222,722; see Figure 29) by providing an interconnect through the opening formed in the second substrate oxide layer to connect to the second electrode. This is because of the desirability and necessary to provide electrical connection to the second electrode so that the device can be properly operated. Furthermore, forming the first and second electrodes having a non-smooth surface would have been obvious as taught by Fukuzumi, since it would increase the capacitor plate area. Furthermore, Chu et al (5,856,937) teach forming a computer system having processors including capacitor and memory devices including capacitors, wherein the first device and second device are connected via a bus (at col 10, lines 20-65; col 1, lines 16-67; Figs 2-4; col 6-8). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to employ the capacitor as made by Fukuzumi to form a computer system having processors and memory devices as taught by Chu et al. This is because of the desirability to form a computer system for storing and processing information, wherein the processors having capacitors are central processing unit for processing data for operation, and wherein the memory devices having capacitors are used for accessing data stored in the capacitors.

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b), and be timely submitted.

Response to Amendment

4. Applicant submitted (at remark filed February 02, 2005) the statement that the present application and the Agarwal reference "...were, the time the present invention was made, owned by, or subject to an obligation of assignment to, the same person...". Accordingly, the U.S. Patent 6,165,834 of Agarwal is disqualified as prior art through 35 U.S.C. 102(e), (f) or (g) in any rejection under 35 U.S.C. 103(a) in this present application.

5. Applicant's other remarks and amendment filed February 02, 2005 with respect to the claims have been considered, but they are moot in view of the new ground(s) of rejection.

Heating the dielectric layer in the presence of oxygen-containing ambient would have been obvious to one of ordinary skill in the art, at least as taught by New (5,824,590).

In response to Applicant's analysis of the references, the rejection is not overcome by pointing out that one reference does not contain a particular limitation when reliance for that teaching is on another reference. In Re Lyons 150 USPQ 741 (CCPA 1966). Moreover, it is well settled that one can not show non-obviousness by attacking the references individually where, as here, the rejection is based on combinations of references. In Re Keller, 208 USPQ 871 (CCPA 1981); In Re Young, 159 USPQ 725 (CCPA 1968).

The Examiner recognizes that references cannot be arbitrarily combined and that there must be some logical reason why skilled in the art would be motivated to make the proposed combination of references. In re Regel 188 USPQ 136 (CCPA 1975). The test for combining references is what the combination of disclosures taken as a whole would suggest to one of ordinary skill in the art. IN re McLaughlin 170 USPQ 209 (CCPA 1971); IN Re Rosselet 146 USPQ 183 (CCPA 196). References are evaluated by what they collectively suggest to one versed in the art, rather than by their specific disclosures. In Re Simon, 174 USPQ 114 (CCPA 1972); In Re Richman 165 USPQ 509, 514 (CCPA 1970).

The prior art motivation or advantage may be different than that of applicant while still supporting a conclusion of obviousness. In Re Wiseman 201 USPQ 658 (CCPA 1979); Ex Parte Obiaya 227 USPQ 58 (Bd. of App. 1985).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michael M. Trinh whose telephone number is (571) 272-1847. The examiner can normally be reached on M-F: 8:30 Am to 5:00 Pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application should be directed to the receptionist whose telephone number is (703) 308-0956.

Oacs-6



Michael Trinh
Primary Examiner